

Supporting Information

Three-Dimensional MoS₂ Nanosheet Structures: CVD Synthesis, Characterization, and Electrical Properties

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Figure S1. Schematic illustration of the CVD setup.

Figure S2. Cross-sectional FIB image of vertical MoS₂.

Figure S3 Raman spectrum obtained with different growth time.

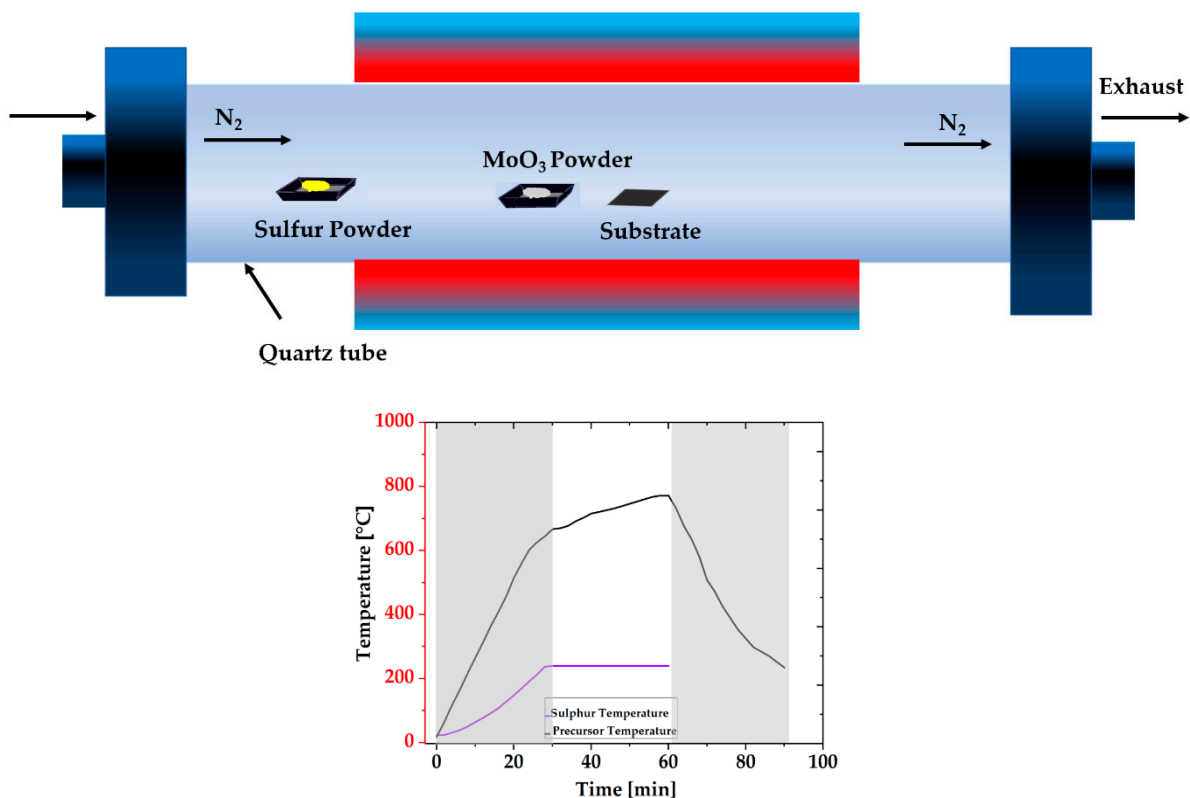


Figure S1. Schematic illustration of the CVD setup used for the preparation of vertical MoS_2 thin films and its temperature profile.

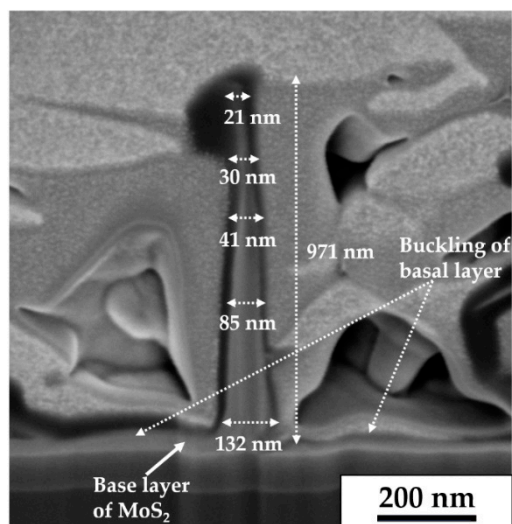


Figure S2. Cross-sectional FIB image of vertical MoS_2 with a tapered geometry. Thickness of the vertical structure from the base to the top is illustrated.

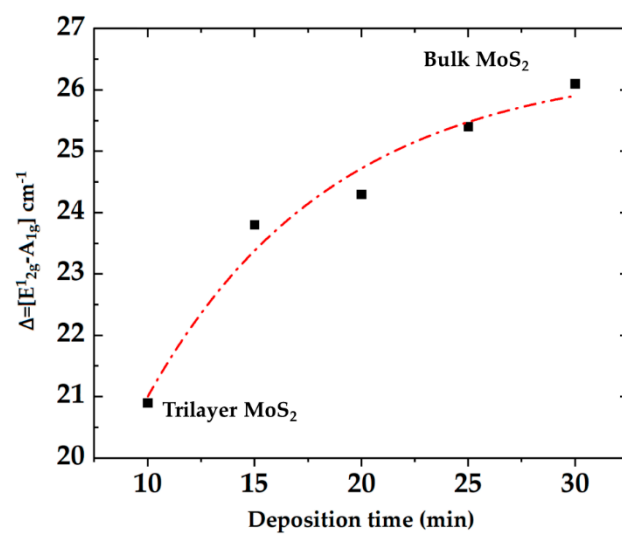


Figure S3 Frequency difference between E^{12g} and A^{1g} peaks for different deposition time illustrates a transition from a two-dimensional to a three-dimensional state.